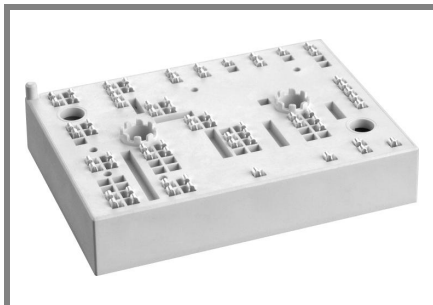


# SKiiP 38NAB066V1



## MiniSKiiP<sup>®</sup>3

3-phase bridge rectifier +  
brake chopper + 3-phase  
bridge inverter  
**SKiiP 38NAB066V1**

### Features

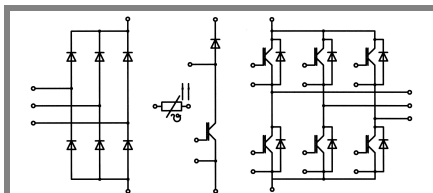
- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

### Typical Applications

- Inverter up to 22 kVA
- Typical motor power 11 kW

### Remarks

- Case temperature limited to  $T_C = 125^\circ\text{C}$  max.
- Product reliability results are valid for  $T_j = 150^\circ\text{C}$
- SC data:  $t_p \leq 6 \mu\text{s}$ ;  $V_{GE} \leq 15 \text{ V}$ ;  $T_j = 150^\circ\text{C}$ ;  $V_{CC} = 360 \text{ V}$
- $V_{CEsat}$ ,  $V_F =$  chip level value



NAB

Absolute Maximum Ratings		$T_S = 25^\circ\text{C}$ , unless otherwise specified	
Symbol	Conditions	Values	Units
<b>IGBT - Inverter, Chopper</b>			
$V_{CES}$		600	V
$I_C$	$T_S = 25 (70)^\circ\text{C}$ , $T_j = 150^\circ\text{C}$	101 (68)	A
$I_C$	$T_S = 25 (70)^\circ\text{C}$ , $T_j = 175^\circ\text{C}$	112 (83)	A
$I_{CRM}$	$t_p = 1 \text{ ms}$	200	A
$V_{GES}$		$\pm 20$	V
<b>Diode - Inverter, Chopper</b>			
$I_F$	$T_S = 25 (70)^\circ\text{C}$ , $T_j = 150^\circ\text{C}$	103 (67)	A
$I_F$	$T_S = 25 (70)^\circ\text{C}$ , $T_j = 175^\circ\text{C}$	112 (81)	A
$I_{FRM}$	$t_p = 1 \text{ ms}$	200	A
<b>Diode - Rectifier</b>			
$V_{RRM}$		800	V
$I_F$	$T_S = 70^\circ\text{C}$	61	A
$I_{FSM}$	$t_p = 10 \text{ ms}$ , $\sin 180^\circ$ , $T_j = 25^\circ\text{C}$	700	A
$i^2t$	$t_p = 10 \text{ ms}$ , $\sin 180^\circ$ , $T_j = 25^\circ\text{C}$	2400	$\text{A}^2\text{s}$
$I_{tRMS}$	per power terminal (20 A / spring)	80	A
$T_j$	IGBT, Diode	-40...+175	$^\circ\text{C}$
$T_{stg}$		-40...+125	$^\circ\text{C}$
$V_{isol}$	AC, 1 min.	2500	V

Characteristics		$T_S = 25^\circ\text{C}$ , unless otherwise specified			Units
Symbol	Conditions	min.	typ.	max.	Units
<b>IGBT - Inverter, Chopper</b>					
$V_{CE(sat)}$	$I_{Cnom} = 100 \text{ A}$ , $T_j = 25 (150)^\circ\text{C}$	1,05	1,45 (1,65)	1,85 (2,05)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 2 \text{ mA}$		5,8		V
$V_{CE(TO)}$	$T_j = 25 (150)^\circ\text{C}$		0,9 (0,8)	1,1 (1)	V
$r_{CE}$	$T_j = 25 (150)^\circ\text{C}$		5,5 (8,5)	7,5 (10,5)	$\text{m}\Omega$
$C_{ies}$	$V_{CE} = 25 \text{ V}$ , $V_{GE} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		6,15		nF
$C_{oes}$	$V_{CE} = 25 \text{ V}$ , $V_{GE} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		1,12		nF
$C_{res}$	$V_{CE} = 25 \text{ V}$ , $V_{GE} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		0,9		nF
$R_{CC+EE'}$	spring contact-chip $T_S = 25 (150)^\circ\text{C}$				$\text{m}\Omega$
$R_{th(j-s)}$	per IGBT		0,6		K/W
$t_{d(on)}$	under following conditions		40		ns
$t_r$	$V_{CC} = 300 \text{ V}$ , $V_{GE} = -8\text{V}/+15\text{V}$		40		ns
$t_{d(off)}$	$I_{Cnom} = 100 \text{ A}$ , $T_j = 150^\circ\text{C}$		410		ns
$t_f$	$R_{Gon} = R_{Goff} = 8,2 \Omega$		50		ns
$E_{on} (E_{off})$	inductive load		3,4 (3,5)		mJ
<b>Diode - Inverter, Chopper</b>					
$V_F = V_{EC}$	$I_F = 100 \text{ A}$ , $T_j = 25 (150)^\circ\text{C}$		1,3 (1,3)	1,5 (1,5)	V
$V_{(TO)}$	$T_j = 25 (150)^\circ\text{C}$		0,9 (0,8)	1 (0,9)	V
$r_T$	$T_j = 25 (150)^\circ\text{C}$		4 (5)	5 (6)	$\text{m}\Omega$
$R_{th(j-s)}$	per diode		0,8		K/W
$I_{RRM}$	under following conditions		102		A
$Q_{rr}$	$I_{Fnom} = 100 \text{ A}$ , $V_R = 300 \text{ V}$		15,4		$\mu\text{C}$
$E_{rr}$	$V_{GE} = 0 \text{ V}$ , $T_j = 150^\circ\text{C}$		3,3		mJ
	$di_F/dt = 2560 \text{ A}/\mu\text{s}$				
<b>Diode - Rectifier</b>					
$V_F$	$I_{Fnom} = 35 \text{ A}$ , $T_j = 25^\circ\text{C}$		1,1		V
$V_{(TO)}$	$T_j = 150^\circ\text{C}$		0,8		V
$r_T$	$T_j = 150^\circ\text{C}$		11		$\text{m}\Omega$
$R_{th(j-s)}$	per diode		0,9		K/W
<b>Temperature Sensor</b>					
$R_{ts}$	3 %, $T_r = 25 (100)^\circ\text{C}$		1000(1670)		$\Omega$
<b>Mechanical Data</b>					
w			97		g
$M_s$	Mounting torque	2		2,5	Nm

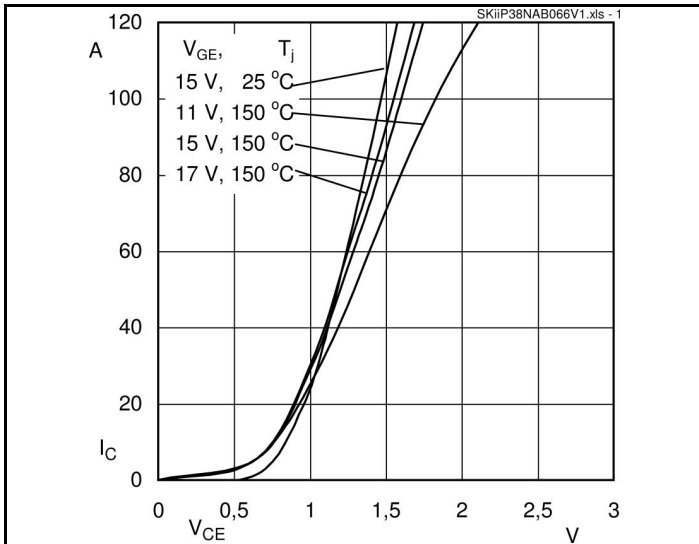


Fig. 1 Typ. output characteristic

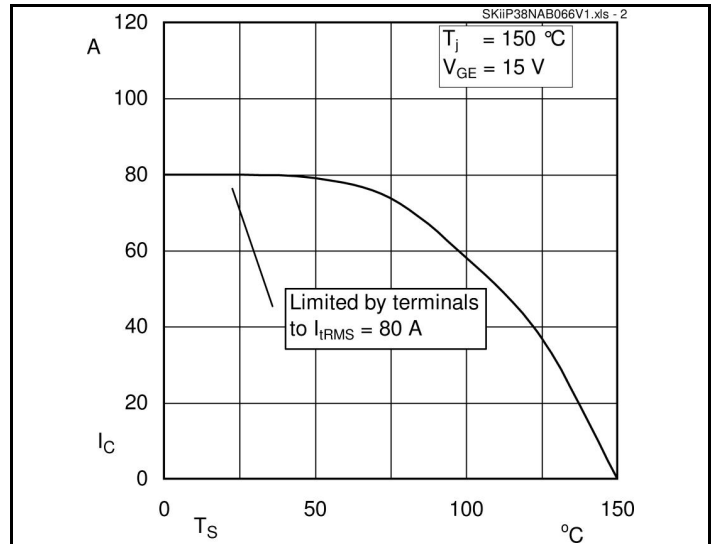


Fig. 2 Typ. rated current vs. temperature

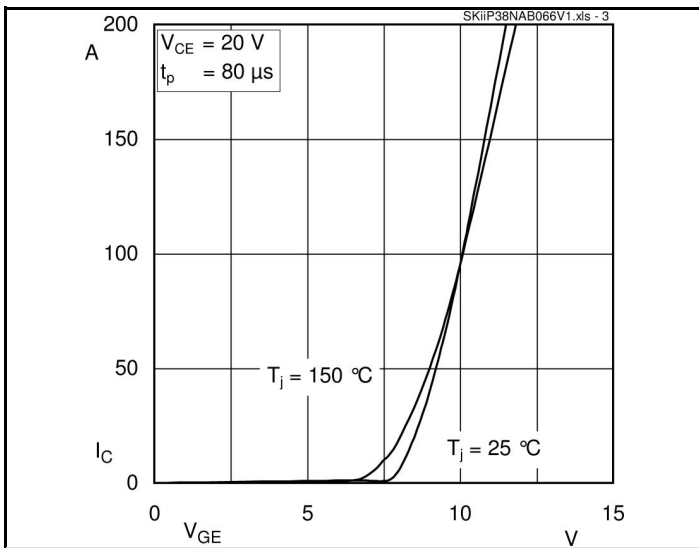


Fig. 3 Typ. transfer characteristic

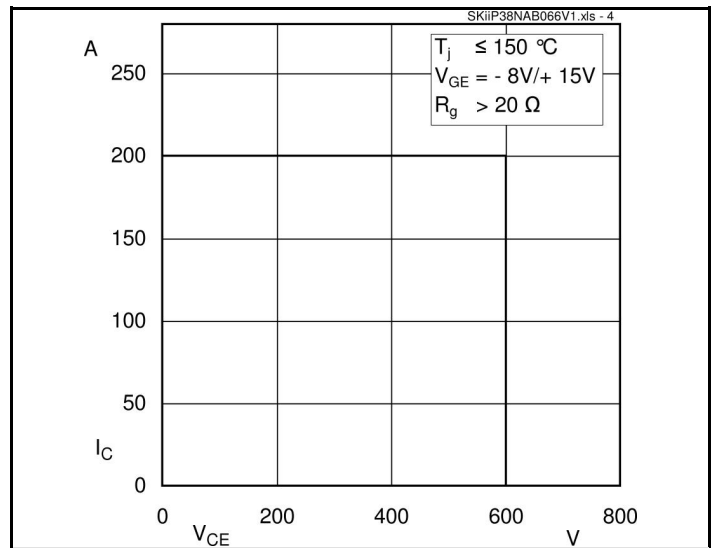


Fig. 4 Reverse bias safe operating area

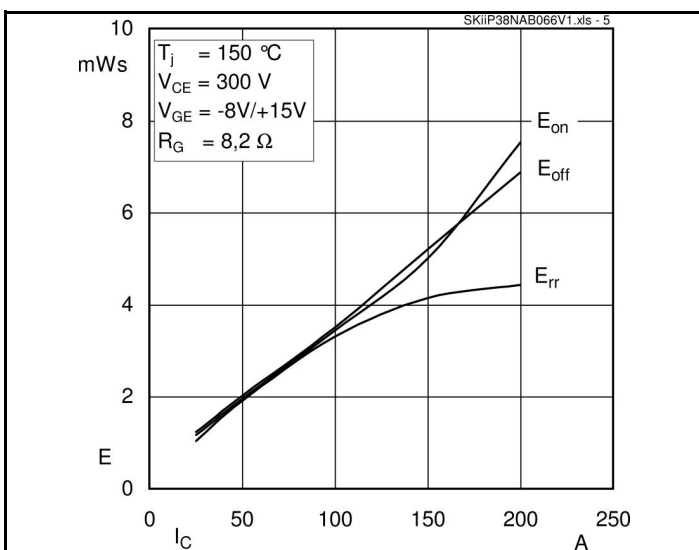


Fig. 5 Typ. turn-on /-off energy =  $f(I_C)$

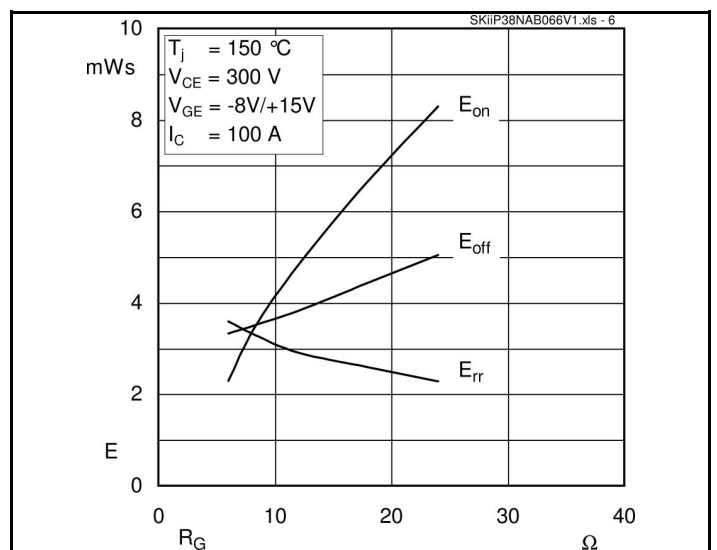
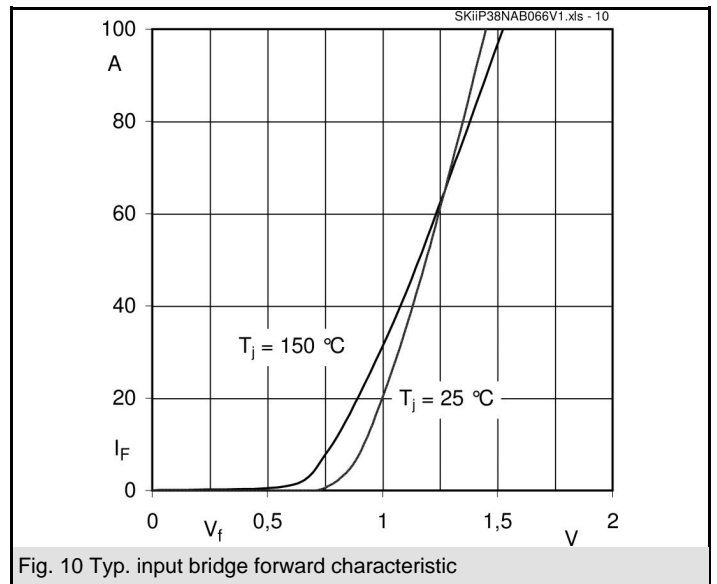
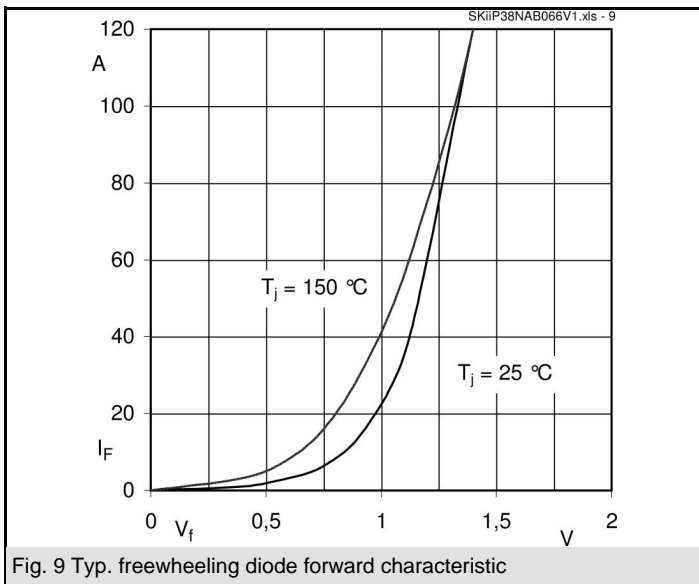
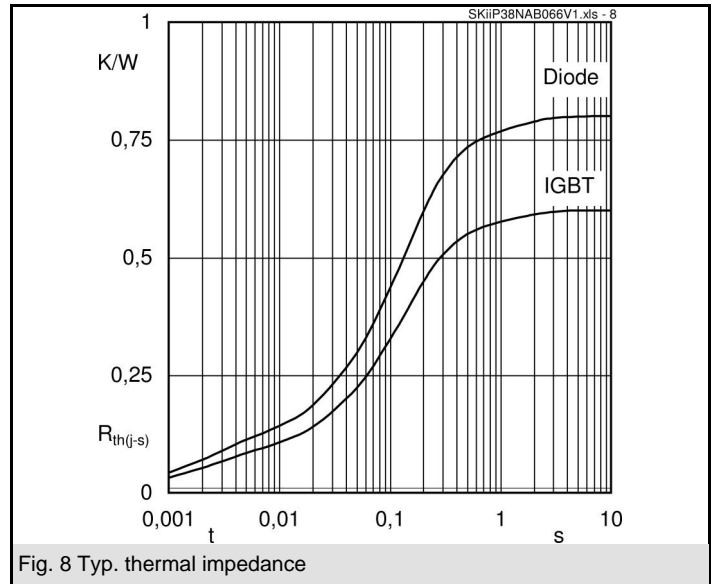
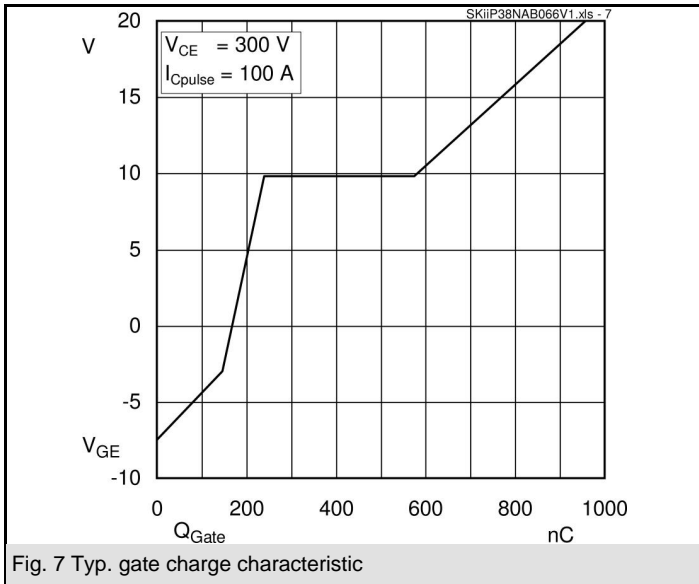
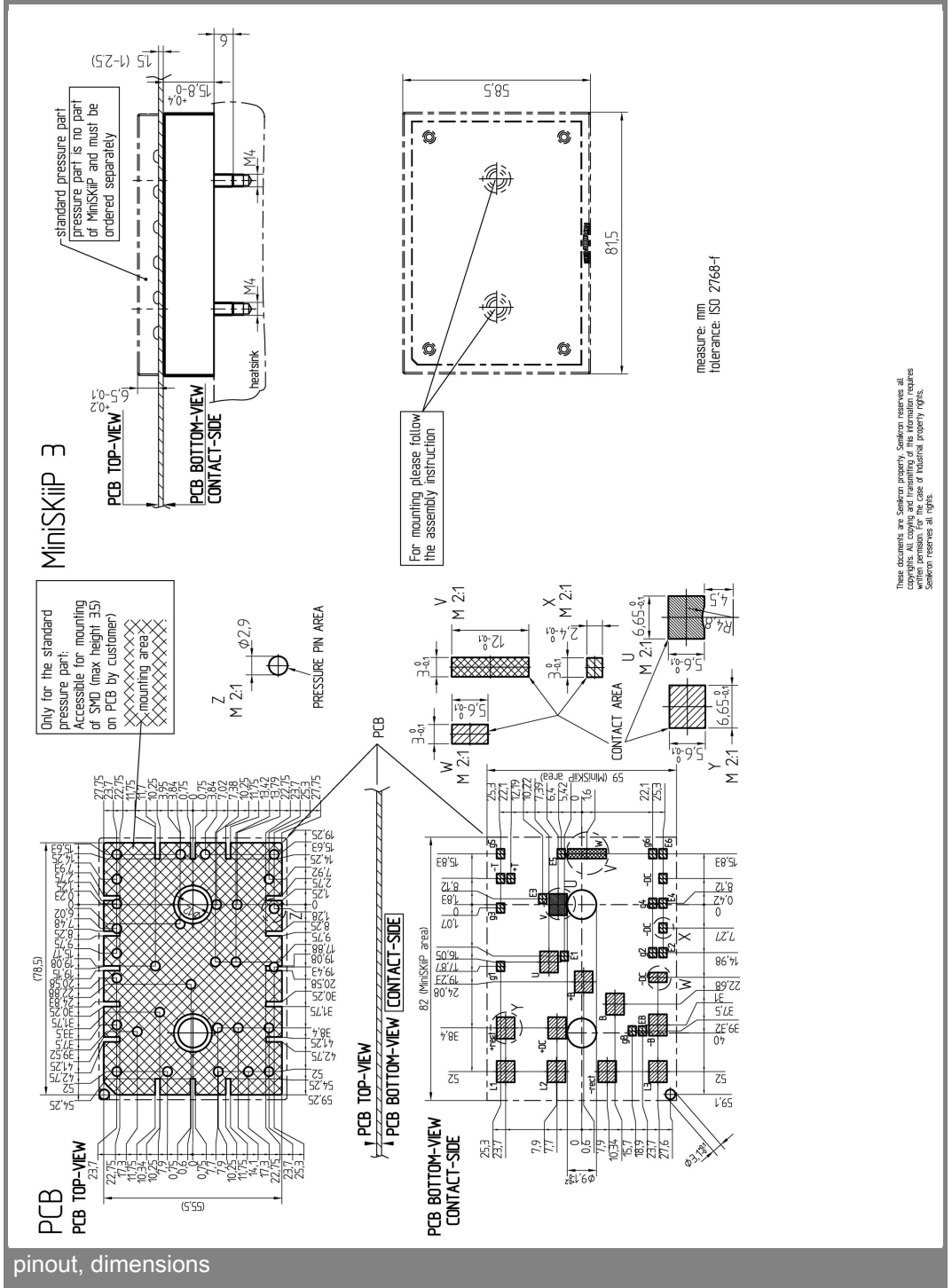
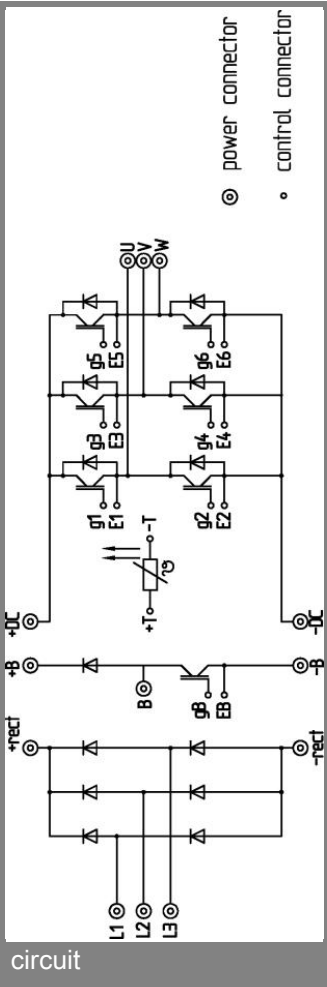


Fig. 6 Typ. turn-on /-off energy =  $f(R_G)$





This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.